

1N4001 THRU 1N4007
1.0 SILICON RECTIFIER

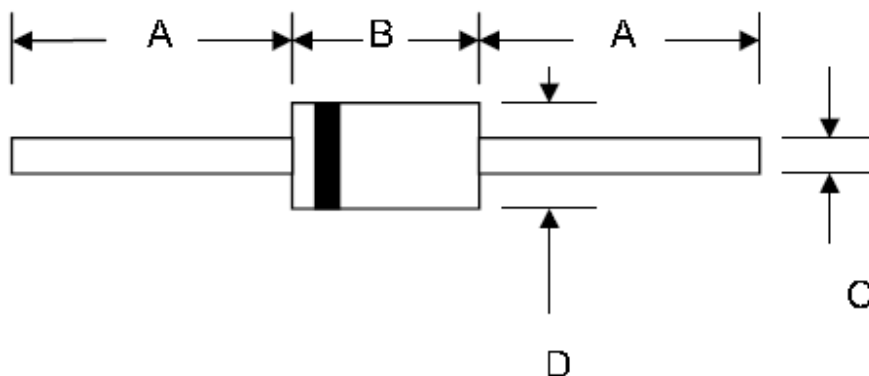
Features:

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical data:

- Case: Molded Plastic
- Terminals: Plated Leads Solderable Per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams(Approx)
- Mounting Position: Any

Mechanical Dimensions: In mm/Inches



DO-41				
Dim	Min	Max	Min	Max
A	25.4	—	1.000	—
B	4.06	5.21	0.159	0.205
C	0.71	0.864	0.028	0.034
D	2.00	2.72	0.079	0.107
	In mm		In inch	

DO-41



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Technical Data
Data Sheet N0543, Rev. -

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Marking Diagram:

Where XXXXX is YYWWL



1N4001 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL: 94V-0

Ordering Information

Device	Package	Shipping
1N4001-1N4007	DO-41 (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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- China - Germany - Korea - Singapore - United States •
 - <http://www.smc-diodes.com> - sales@smc-diodes.com •

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Type Number	Symbol	1N 4001	1N 4002	1N 4003	1N 4004	1N 4005	1N 4006	1N 4007	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current @T _A = 75°C	I _O	1.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30							A
Forward Voltage @I _F = 1.0A	V _{FM}	1.0							V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5.0 50							μA
Typical Junction Capacitance (Note 2)	C _J	15							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}	50							°C/W
Operating Junction Temperature Range	T _J	-65 to +125							°C
Storage Temperature Range	T _{STG}	-65 to +150							°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

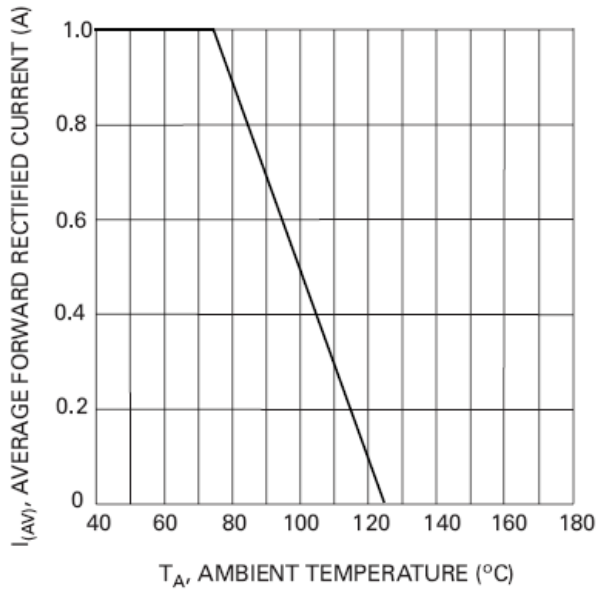


Fig. 1 Forward Current Derating Curve

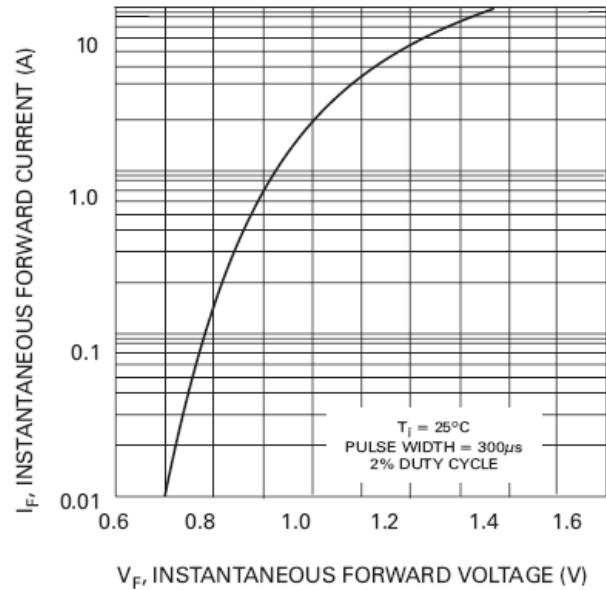


Fig. 2 Typical Forward Characteristics

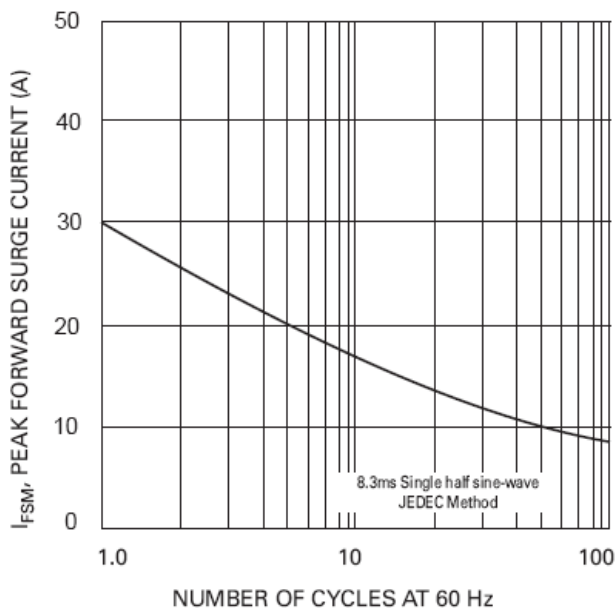


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

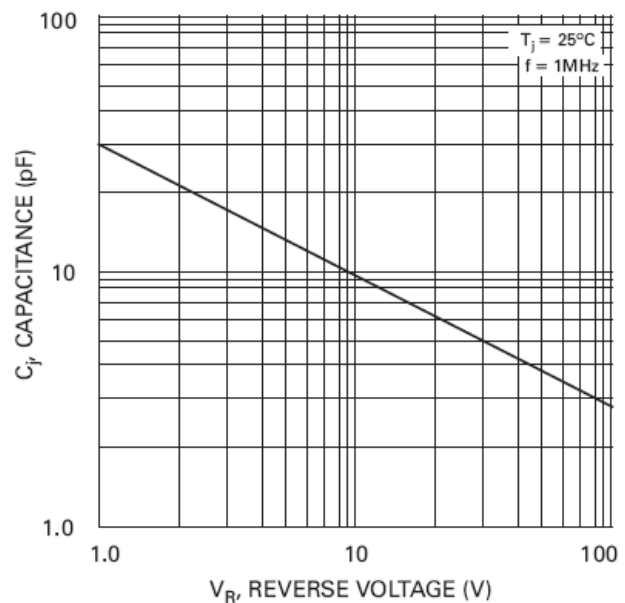


Fig. 4 Typical Junction Capacitance



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